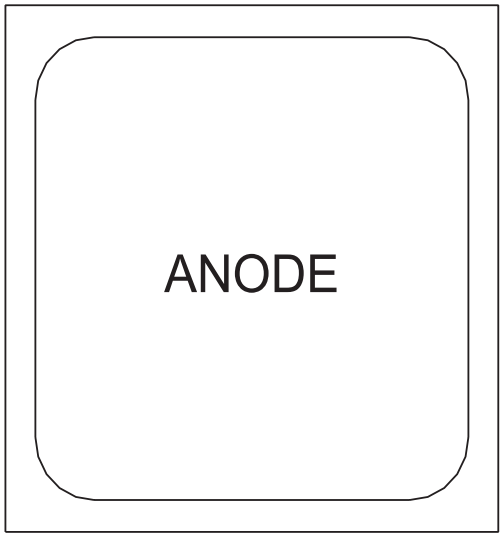
Central™
Semiconductor Corp.

PROCESS CPD25
Fast Recovery Rectifier
3 Amp Glass Passivated Rectifier Chip

PROCESS DETAILS

Process	GLASS PASSIVATED MESA
Die Size	87 x 87 MILS
Die Thickness	10.6 MILS
Anode Bonding Pad Area	69.5 x 69.5 MILS
Top Side Metalization	Au - 5,000Å
Back Side Metalization	Au - 2,000Å

GEOMETRY



BACKSIDE CATHODE

R0

GROSS DIE PER 4 INCH WAFER
1,490

PRINCIPAL DEVICE TYPES
1N5185 thru 1N5188
1N5415 thru 1N5420

The Typical Electrical Characteristics data for this chip is currently being revised.

For the latest updated data for this Chip Process, please visit our website at:

www.centralsemi.com/chip

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R1 (1-August 2002)